CONTENTS

Glukhova O. E., Kolesnikova A. S. Emission Properties of Potassium-Doped Bamboo-Like Nanotubes 2 At first, the emission capability of the infinite bamboo-like carbon nanotubes with the smallest diameter was investigated. The bamboo-like carbon nanotube emission properties were calculated using the tight-binding quantium-chemical method. It was shown that the infinite bamboo-like nanotube with a specific distance between the bridges (2,811 nm) has a better emission property in comparison with the hollow ones. It was established that the aforementioned properties of the bamboo-like carbon nanotubes were improved by doping them with the potassium atoms. It should be mentioned that the potassium atoms concentration should exceed 0,59 %. The work function of the infinite bamboo-like carbon nanotubes with the added potassium atoms has reduced to 0,178 eV.

Keywords: bamboo-like nanotubes, the potassium atoms, the ionization potential, nanoemittery, emission capability, the work function

Korostelev V. F., Khomova L. P. Research of Influence of Pressure upon Crystallization and Change of Nanostructure of Aluminum..... 6 Kristallogeometrichesky, thermodynamic and nanostructural aspects of the theory of crystallization are considered.

It is established that increase of the pressure imposed on melt from 400 to 500 MPa provides decrease in density of dislocations thanks to formation of nanocrystals with the sizes 12...40 nm with almost faultless structure.

Data on change of a limit of fluidity and the module the Ship's boy are provided.

Keywords: appearing-through electronic microscopy, a structure of borders of grains, crystallization model, interatomic communications and interactions, structure formation from nanocrystals

Latokhin D. V., Konovalov A. V., Voronkov E. N. Estimation of the Parameters to Barrier in Nanocrystalline In this paper we report about the methodology, which on the basis of the temperature dependence of electrical conductivity and barrier model nanocrystalline semiconductor film can be estimated barrier height, their concentration and crystallite size. Application of the proposed method of calculation to nanocrystalline films Si:H has given satisfactory results.

Keywords: semiconductors, nanocrystallites, hydrogenated silicon, electrical conductivity

Chelpanov I. B., Kochetkov A. V. System-Focused Processing of Results of Tests Microelektronnomehanichesky Circle of questions of planning, organization and carrying out of tests of micromechanical gages and devices, first of all the micromechanical gyroscopes which are a part of navigating systems and complexes of mobile objects. **Keywords:** micromechanical devices, tests, gages, gages of angular speed, acceleration gages

Voronin O. G., Konishcheva E. V., Zorin N. A., Fedotenkov F. A., Karyakina E. E., Karpacheva G. P., Orlov A. V., Kiseleva S. G., Karyakin A. A. Modification of the Electrode Surface with Analogues of Hydrogenase Novel methods for development of highly active nanobioelectrodes based on surface modification or hydrogenase entrapment into matrix were elaborated. It was shown that modification of the electrode surface with electroactive polymers containing analogues of hydrogenase substrates leads to significant increase of activity. Comparison of the electrodes based on different enzyme (nanobiocatalyst) immobilization methods was conducted. **Keywords:** biofuel cell, hydrogenase, enzyme electrode, hydrogen

Yuzeeva N. A. Electron Mobility in $In_{0,52}Al_{0,48}As/In_{0,53}Ga_{0,47}As$ HEMT Structures on InP Substrate....19 The influence of the quantum well width d on the electron mobility was investigated in the $In_{0,52}Al_{0,48}As/In_{0,53}Ga_{0,47}As$ quantum well on InP substrate. A mobility depends on d nonmonotonically with a maximal value 53 500 cm²(V · s) for d = 160 Å. Quantum and transport electron mobilities were determined from the Shubnikov – de Haas effect and calculated theoretically. An energy band diagramm was calculated theoretically. It was shown that a charged impurity scattering is dominant.

Keywords: HEMT, InAlAs/InGaAs, InP substrate, quantum well, energy band diagram

Averin I. A., Pronin I. A., Karmanov A. A. The Study of a Gas-Sensitive Sensors Based on Nanostructured mechanisms of conduction and hemoresistive response of composites are investigated, the parameters corresponding to maximum sensitivity film SiO_2 — SnO_2 are defined. **Keywords:** conductance, sensitivity, vacancy, hemoresistive processes, sol-gel technology, fractals

Constructive of parallel-sided electrostatic micro actuator, which more comprehensive series of independent functions of control and monitoring is offered.

Keywords: electrostatic micro actuator, parallel-sided structure, independent functions of control and monitoring

Keywords: RFID, SAW, IDT, lift-off lithography, photoresist

Keywords: magnetic field sensor, Ampere force, piezoelectric effect, lead zirconate titanate

Keywords: gas chemical nanosensor, sensing element, polymer, constructional characteristic, metrological characteristic

A new interpretation of human brain as an organic hybrid nanoelectronics object created by Nature is presented. The nearest analogue in artificial electronics is an integrated circuit of micro- and nanoelectronics. Therefore the comparison of the neuronal circuits of the brain with integrated circuits was made and their basic differences were determined. The proposed interpretation and its consequences allow, on the one hand, to analyze the principles of the brain functioning more deeply, and, on the other — to suggest a complex approach of brain investigation, based on multilevel simulation combined with experimental methods. In the part III the answers to the following questions are presented: "Is quantum mechanics enough for description of the brain functioning, including consciousness, thought, and its other mental functions? How to investigate the brain farther?"

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